



High Speed CMOS Logic – 74HC30

8-Input NAND Gate IC in bare die form

Rev 1.0
7/5/2019

Description

The 74HC30 8-Input NAND Gate is made using a 2.5µm 5V CMOS process & combines the high speed of LSTTL with CMOS low power consumption. The device performs Boolean functions in positive logic:

$$Y = A \cdot B \cdot C \cdot D \cdot E \cdot F \cdot G \cdot H \text{ or}$$
$$Y = \overline{A + B + C + D + E + F + G + H}$$

Device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs. Internal circuitry comprises 3 stages & includes buffered output for high noise immunity & stability.

Ordering Information

The following part suffixes apply:

- No suffix - MIL-STD-883 /2010B Visual Inspection

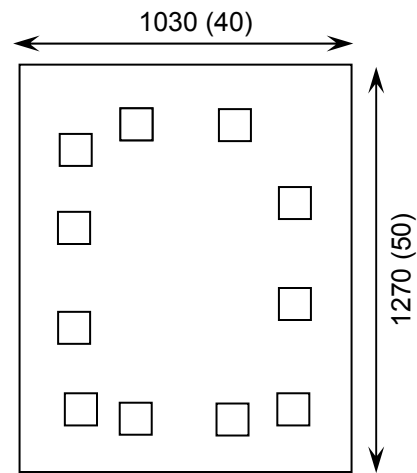
For High Reliability versions of this product please see

[54HC30](#)

Features:

- Low Input Current: 1µA
- Output Drive Capability: 10 LSTTL loads
- Outputs Directly Interface to CMOS, NMOS, & TTL
- Operating Voltage Range: 2V to 6V
- CMOS High Noise Immunity
- Function compatible with 74LS30.

Die Dimensions in µm (mils)



Supply Formats:

- Default – Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape – On request
- Unsawn Wafer – On request
- Die Thickness <=> 350µm(14 Mils) – On request
- Assembled into Ceramic Package – On request

Mechanical Specification

Die Size (Unsawn)	1030 x 1270 40 x 50	µm mils
Minimum Bond Pad Size	108 x 108 4.25 x 4.25	µm mils
Die Thickness	350 (±20) 13.78 (±0.79)	µm mils
Top Metal Composition	Al 1%Si 1.1µm	
Back Metal Composition	N/A – Bare Si	

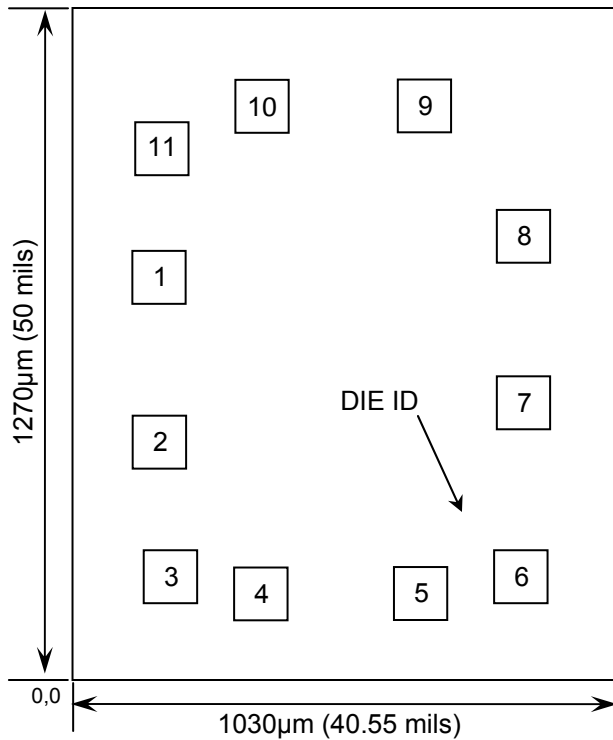




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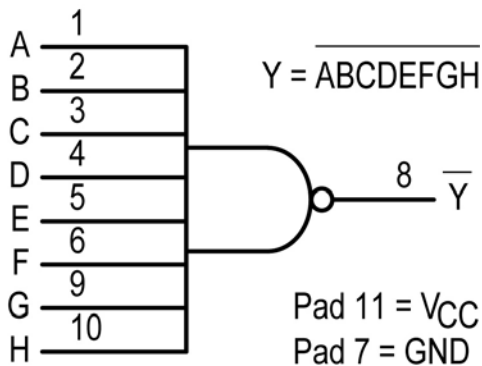
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Pad Layout and Functions



PAD	FUNCTION	COORDINATES (mm)	
		X	Y
1	A	0.1155	0.7200
2	B	0.1155	0.4015
3	C	0.1355	0.1465
4	D	0.3080	0.1160
5	E	0.6220	0.1160
6	F	0.8130	0.1465
7	GND	0.8130	0.4810
8	\bar{Y}	0.8130	0.8000
9	G	0.6220	1.0465
10	H	0.3080	1.0465
11	V _{CC}	0.1155	0.9670
CONNECT CHIP BACK TO V _{CC} OR FLOAT			

Logic Diagram



Function Table

INPUTS								OUTPUT
A	B	C	D	E	F	G	H	Y
L	X	X	X	X	X	X	X	H
X	L	X	X	X	X	X	X	H
X	X	L	X	X	X	X	X	H
X	X	X	L	X	X	X	X	H
X	X	X	X	L	X	X	X	H
X	X	X	X	X	L	X	X	H
X	X	X	X	X	X	L	X	H
X	X	X	X	X	X	X	L	H
H	H	H	H	H	H	H	H	L

H = High level (steady state)
L = Low level (steady state)
X = don't care





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Absolute Maximum Ratings¹

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage (Referenced to GND)	V_{CC}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	V_{IN}	-1.5 to $V_{CC} + 1.5$	V
DC Output Voltage (Referenced to GND)	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
DC Input Current, per pad	I_{IN}	± 20	mA
DC Output Current, per pad	I_{OUT}	± 25	mA
DC Supply Current, V_{CC} or GND, per pad	I_{CC}	± 50	mA
Power Dissipation in Still Air ²	P_D	750	mW
Storage Temperature Range	T_{STG}	-65 to 150	$^{\circ}C$

1. Operation above the absolute maximum rating may cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plastic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS	
Supply Voltage	V_{CC}	2	6	V	
DC Input or Output Voltage	V_{IN}, V_{OUT}	0	V_{CC}	V	
Operating Temperature Range	T_J	-40	+85	$^{\circ}C$	
Input Rise or Fall Times	t_r, t_f	$V_{CC} = 2.0V$	0	1000	ns
		$V_{CC} = 4.5V$	0	500	
		$V_{CC} = 6V$	0	400	

3. This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range $GND \leq (V_{IN} \text{ or } V_{OUT}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC Electrical Characteristics (Voltages referenced to GND)

PARAMETER	SYMBOL	V_{CC}	CONDITIONS	LIMITS			UNITS
				25 $^{\circ}C$	85 $^{\circ}C$	FULL RANGE ⁴	
Minimum High-Level Input Voltage	V_{IH}	2V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$ $ I_{OUT} \leq 20\mu A$	1.5	1.5	1.5	V
		4.5V		3.15	3.15	3.15	
		6.0V		4.2	4.2	4.2	
Maximum Low-Level Input Voltage	V_{IL}	2V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$ $ I_{OUT} \leq 20\mu A$	0.3	0.3	0.3	V
		4.5V		0.9	0.9	0.9	
		6.0V		1.2	1.2	1.2	

4. $-40^{\circ}C \leq T_J \leq +85^{\circ}C$





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DC Electrical Characteristics Continued (Voltages referenced to GND)

PARAMETER	SYMBOL	V _{CC}	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE ⁴	
Minimum High-Level Output Voltage	V _{OH}	2V	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20μA	1.9	1.9	1.9	V
		4.5V		4.4	4.4	4.4	
		6.0V		5.9	5.9	5.9	
		4.5V	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0mA	3.98	3.84	3.84	V
		6.0V		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 5.2mA	5.48	5.34	
Maximum Low-Level Output Voltage	V _{OL}	2V	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20μA	0.1	0.1	0.1	V
		4.5V		0.1	0.1	0.1	
		6.0V		0.1	0.1	0.1	
		4.5V	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0mA	0.26	0.33	0.33	V
		6.0V		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 5.2mA	0.26	0.33	
Maximum Input Leakage Current	I _{IN}	6.0V	V _{IN} = V _{CC} or GND	±0.1	±1.0	±1.0	μA
Maximum Quiescent Supply Current	I _{CC}	6.0V	V _{IN} = V _{CC} or GND, I _{OUT} = 0μA	2	20	20	μA

AC Electrical Characteristics⁵

PARAMETER	SYMBOL	V _{CC}	CONDITIONS	LIMITS			UNITS
				25°C	85°C	FULL RANGE ⁴	
Maximum Propagation Delay, Any Input to Output Y	t _{PLH} , t _{PHL}	2V	C _L = 50pF, t _r = t _f = 6ns	175	220	220	ns
		4.5V		35	44	44	
		6.0V		30	37	37	
Maximum Output Rise and Fall Time, Any Output	t _{TLH} , t _{THL}	2V	C _L = 50pF, t _r = t _f = 6ns	75	95	95	ns
		4.5V		15	19	19	
		6.0V		13	16	16	
Maximum Input Capacitance	C _{IN}	-	-	10	10	10	pF
Power Dissipation Capacitance Per Gate ⁶	C _{PD}	-	T _J = 25°C, V _{CC} = 5.0V	TYPICAL			pF
				27			

5. Not production tested in die form, characterized by chip design and tested in package.

6. Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}.

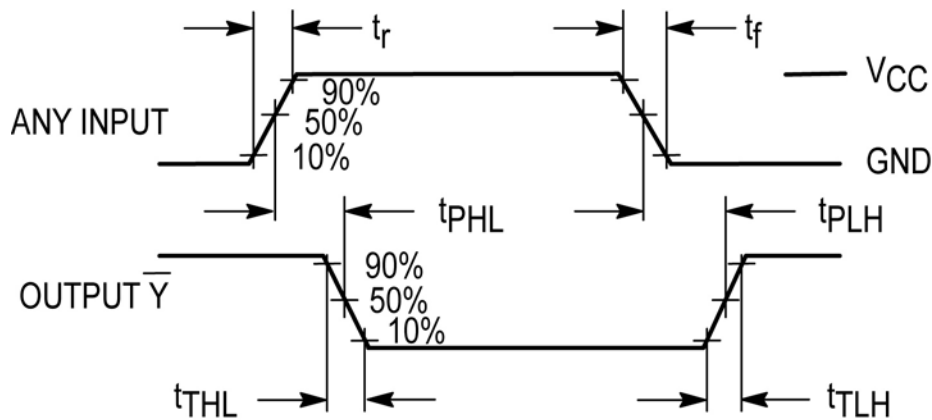




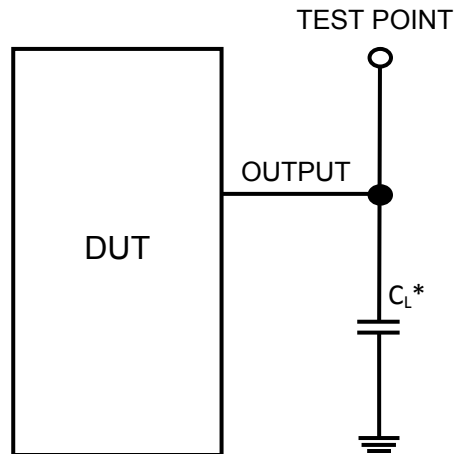
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Switching Waveform



Test Circuit



* Includes all probe and jig capacitance

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